



PSMN1R1-30YLE

N-channel 30 V, 1.3 mOhm, ASFET for hotswap with enhanced SOA in LFAK56

10 November 2022

Product data sheet

1. General description

N-channel enhancement mode ASFET for hotswap with enhanced SOA in LFAK56 package optimized for low R_{DSon} and strong safe operating area, optimized for hot-swap, inrush and linear-mode applications.

2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Optimized for low R_{DSon} / low I^2R conduction losses
- LFAK56 package for applications that demand the highest performance and reliability in a 30 mm² footprint
- Low leakage <1 μ A at 25 °C
- Copper-clip for low parasitic inductance and resistance
- High reliability LFAK package, qualified to 175 °C

3. Applications

- Hot swap in 12 V - 20 V applications
- e-Fuse
- DC switch
- Load switch
- Battery protection

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | - | 30 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2 | [1] | - | 265 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; Fig. 1 | - | - | 192 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Static characteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.01 | 1.26 | mΩ |
| | | $V_{GS} = 7\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.28 | 1.8 | mΩ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 25\text{ A}$; $V_{DS} = 15\text{ V}$; $V_{GS} = 4.5\text{ V}$; $T_j = 25\text{ °C}$; Fig. 12 ; Fig. 13 | 2 | 9 | 18 | nC |
| $Q_{G(tot)}$ | total gate charge | | 13 | 28 | 46 | nC |

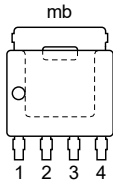
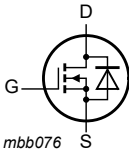
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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|-----------------|---|-----|-----|-----|------|
| Source-drain diode | | | | | | |
| S | softness factor | $I_S = 25 \text{ A}$; $di_S/dt = -100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 15 \text{ V}$; $T_J = 25 \text{ }^\circ\text{C}$; Fig. 16 | - | 1 | - | |

[1] 265 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|---|
| 1 | S | source |  <p>LPAK56; Power-SO8 (SOT669)</p> |  <p>mbb076 S</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|-------------------|--|---------|
| | Name | Description | Version |
| PSMN1R1-30YLE | LPAK56; Power-SO8 | plastic, single-ended surface-mounted package; 4 terminals | SOT669 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|--------------|
| PSMN1R1-30YLE | 1E1L30Y |

8. Limiting values

Table 5. Limiting values

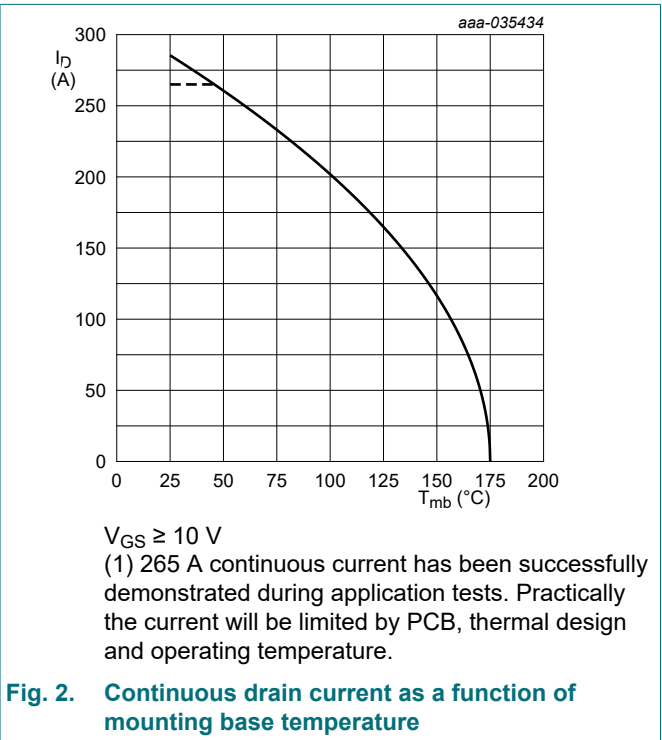
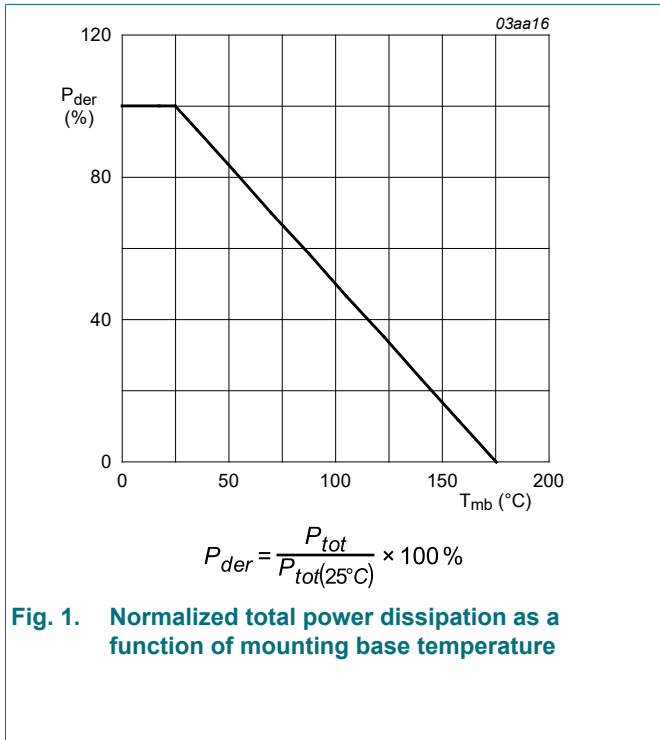
In accordance with the Absolute Maximum Rating System (IEC 60134). $T_J = 25 \text{ }^\circ\text{C}$ unless otherwise stated.

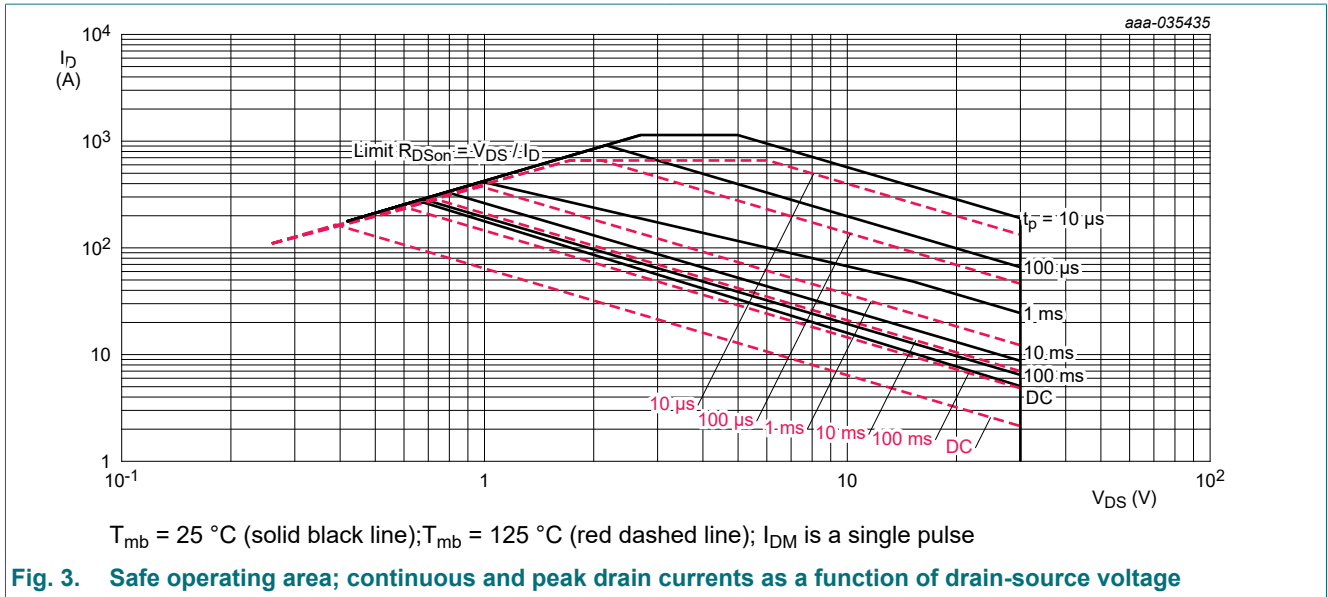
| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|---|-----|------|------------------|
| V_{DS} | drain-source voltage | $25 \text{ }^\circ\text{C} \leq T_J \leq 175 \text{ }^\circ\text{C}$ | - | 30 | V |
| V_{DGR} | drain-gate voltage | $25 \text{ }^\circ\text{C} \leq T_J \leq 175 \text{ }^\circ\text{C}$; $R_{GS} = 20 \text{ k}\Omega$ | - | 30 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 1 | - | 192 | W |
| I_D | drain current | $V_{GS} = 10 \text{ V}$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 2 | [1] | 265 | A |
| | | $V_{GS} = 10 \text{ V}$; $T_{mb} = 100 \text{ }^\circ\text{C}$; Fig. 2 | | 202 | A |
| I_{DM} | peak drain current | pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 3 | - | 1142 | A |
| T_{stg} | storage temperature | | -55 | 175 | $^\circ\text{C}$ |
| T_J | junction temperature | | -55 | 175 | $^\circ\text{C}$ |

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| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|---|-----|------|------|
| $T_{\text{slid(M)}}$ | peak soldering temperature | | - | 260 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{\text{mb}} = 25\text{ °C}$ | - | 192 | A |
| I_{SM} | peak source current | pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{\text{mb}} = 25\text{ °C}$ | - | 1142 | A |
| Avalanche ruggedness | | | | | |
| $E_{\text{DS(AL)S}}$ | non-repetitive drain-source avalanche energy | $I_D = 25\text{ A}$; $V_{\text{sup}} \leq 30\text{ V}$; $R_{\text{GS}} = 50\text{ }\Omega$; $V_{\text{GS}} = 10\text{ V}$; $T_{\text{j(init)}} = 25\text{ °C}$; unclamped; $t_p = 2\text{ ms}$ | [2] | 1 | J |
| I_{AS} | non-repetitive avalanche current | $V_{\text{sup}} \leq 30\text{ V}$; $V_{\text{GS}} = 10\text{ V}$; $T_{\text{j(init)}} = 25\text{ °C}$; $R_{\text{GS}} = 50\text{ }\Omega$ | [2] | 115 | A |

- [1] 265 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test.

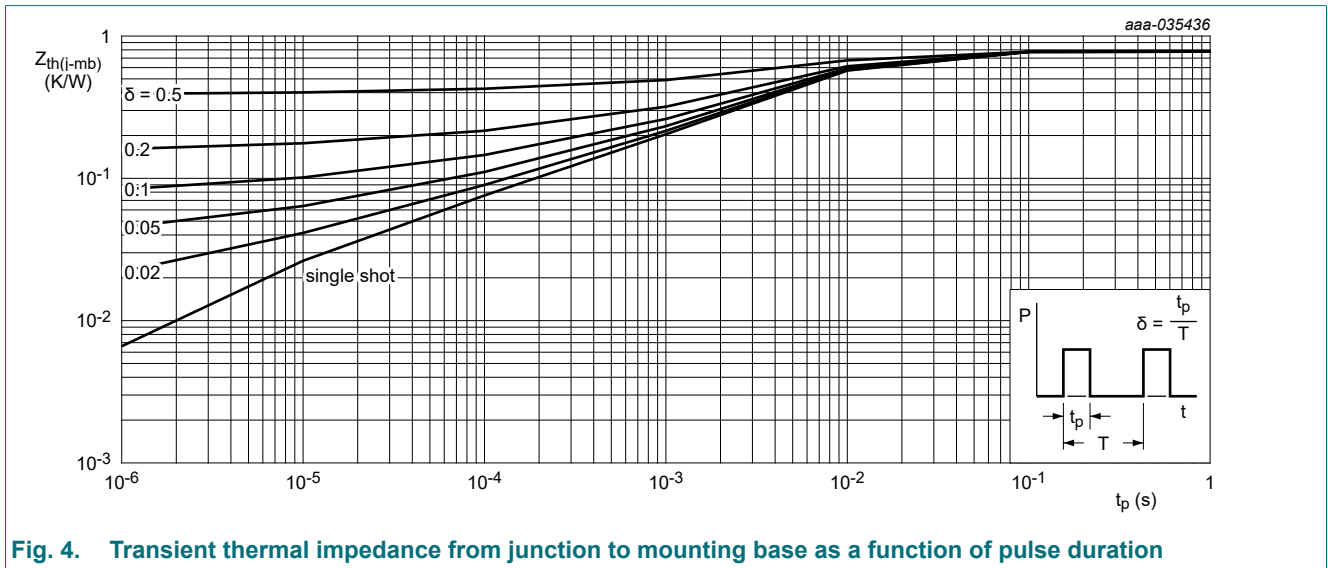


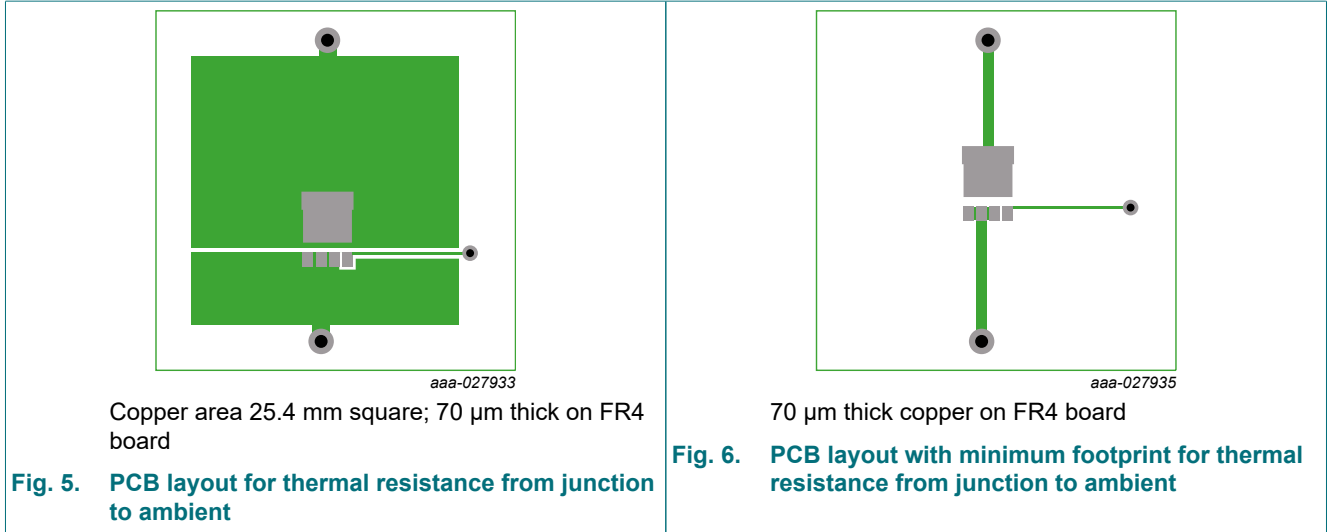


9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------|-----|----------|------|------------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4 | - | 0.38 | 0.78 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 5 Fig. 6 | - | 42 85 | - | K/W K/W |





10. Characteristics

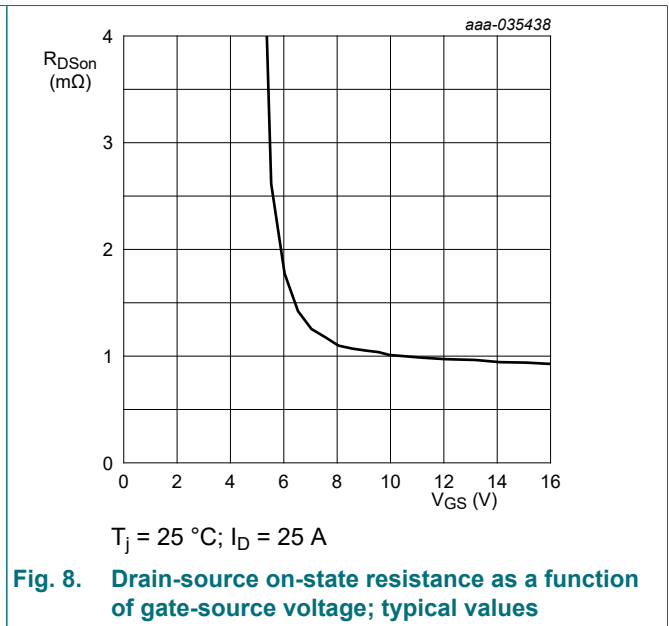
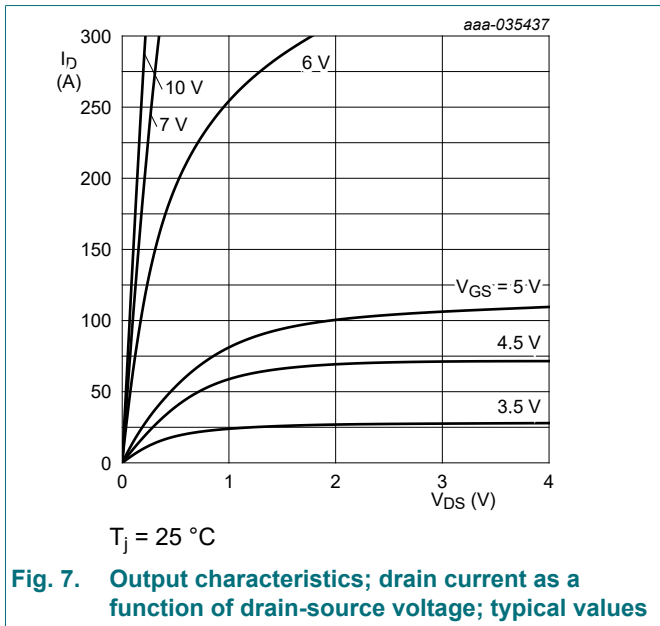
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|--|-----|------|------|------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$ | 30 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 \text{ }^\circ C$ | 27 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_J = 25 \text{ }^\circ C$ | 1.2 | 1.87 | 2.2 | V |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_J \leq 150 \text{ }^\circ C$ | - | -3.7 | - | mV/K |
| I_{DSS} | drain leakage current | $V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$ | - | - | 1 | μA |
| | | $V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 125 \text{ }^\circ C$ | - | 6.4 | - | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$ | - | - | 100 | nA |
| | | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ C$ | - | - | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 25 \text{ }^\circ C;$ Fig. 10 | - | 1.01 | 1.26 | m Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 150 \text{ }^\circ C;$ Fig. 11 | - | - | 2.3 | m Ω |
| | | $V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_J = 25 \text{ }^\circ C;$ Fig. 10 | - | 1.28 | 1.8 | m Ω |
| | | $V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_J = 150 \text{ }^\circ C;$ Fig. 11 | - | - | 3.3 | m Ω |
| R_G | gate resistance | $f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ C$ | 1.2 | 3 | 7.5 | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ $T_J = 25 \text{ }^\circ C;$ Fig. 12 ; Fig. 13 | 13 | 28 | 46 | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ $T_J = 25 \text{ }^\circ C;$ Fig. 12 ; Fig. 13 | 28 | 62 | 102 | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_J = 25 \text{ }^\circ C$ | - | 32 | - | nC |

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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|-----------------------------------|--|------|------|------|------|
| Q_{GS} | gate-source charge | $I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 12; Fig. 13 | 3.5 | 13 | 25 | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | 1.6 | 6 | 12 | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | 1.9 | 7 | 13 | nC |
| Q_{GD} | gate-drain charge | | 2 | 9 | 18 | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25\text{ A}; V_{DS} = 15\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 12; Fig. 13 | - | 3.5 | - | V |
| C_{iss} | input capacitance | $V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C};$ Fig. 14 | 2527 | 4211 | 6317 | pF |
| C_{oss} | output capacitance | | 1019 | 1699 | 2549 | pF |
| C_{riss} | reverse transfer capacitance | | 80 | 296 | 710 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 15\text{ V}; R_L = 0.6\text{ }\Omega; V_{GS} = 4.5\text{ V}; R_{G(ext)} = 5\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$ | - | 35 | - | ns |
| t_r | rise time | | - | 87 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 24 | - | ns |
| t_f | fall time | | - | 32 | - | ns |
| Q_{oss} | output charge | $V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$ | - | 38 | - | nC |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 15 | - | 0.79 | 1 | V |
| t_{rr} | reverse recovery time | $I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16 | - | 31 | - | ns |
| Q_r | recovered charge | | [1] | 23 | - | nC |
| t_a | reverse recovery rise time | | - | 15.7 | - | ns |
| t_b | reverse recovery fall time | | - | 15.6 | - | ns |
| S | softness factor | | - | 1 | - | |

[1] includes capacitive recovery



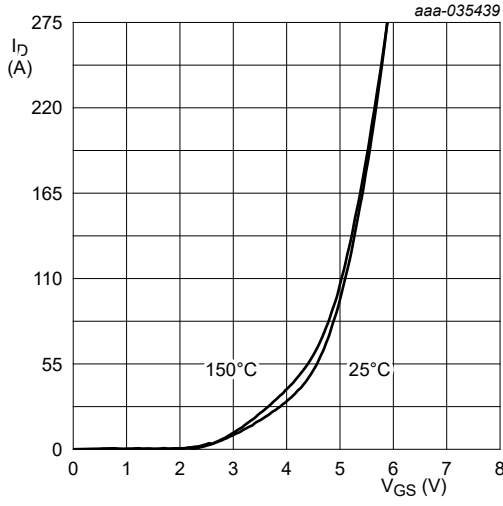


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

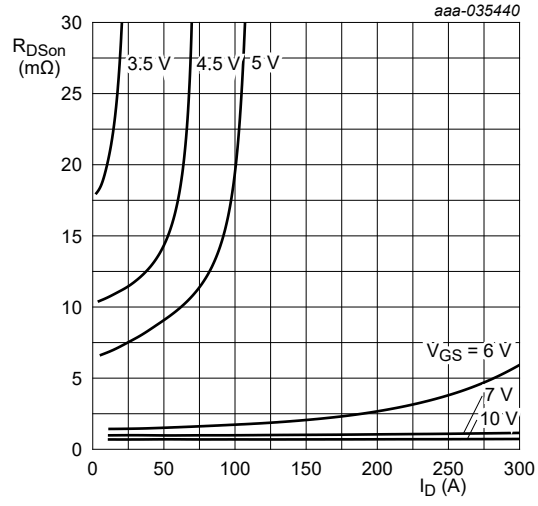
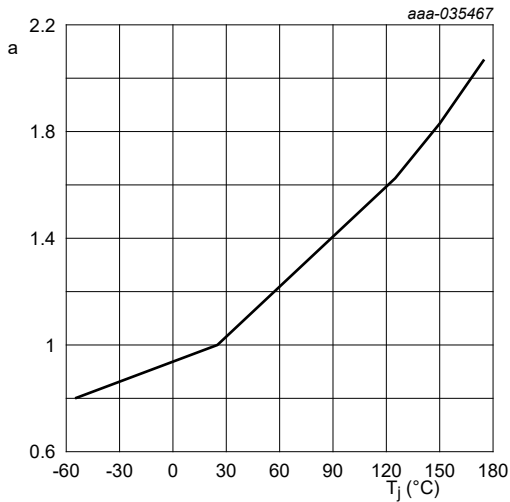


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

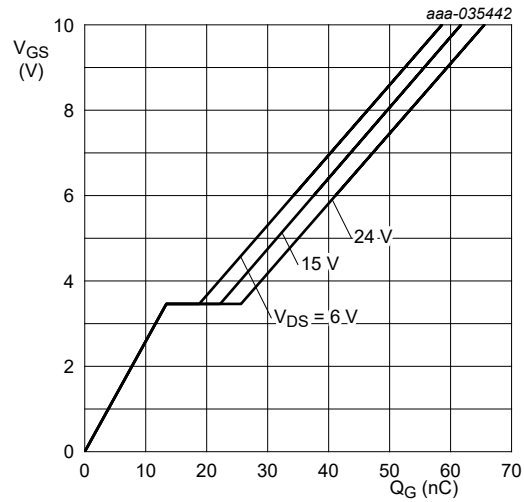


Fig. 12. Gate-source voltage as a function of gate charge; typical values

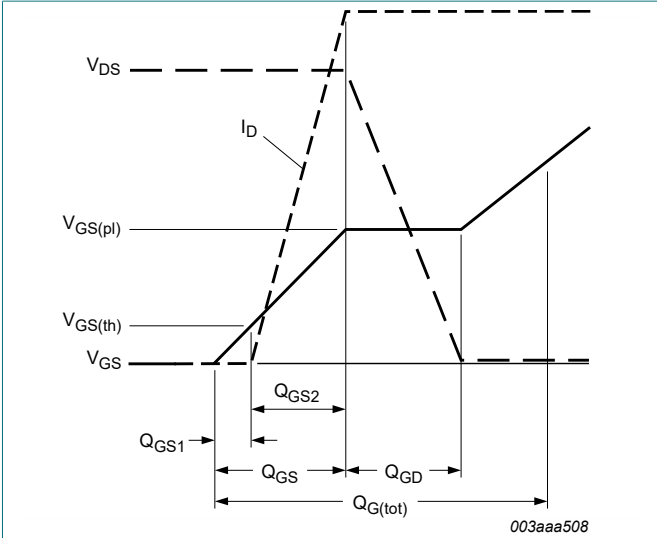


Fig. 13. Gate charge waveform definitions

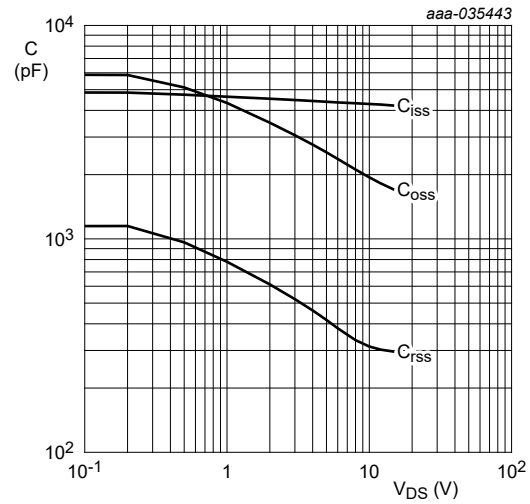


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

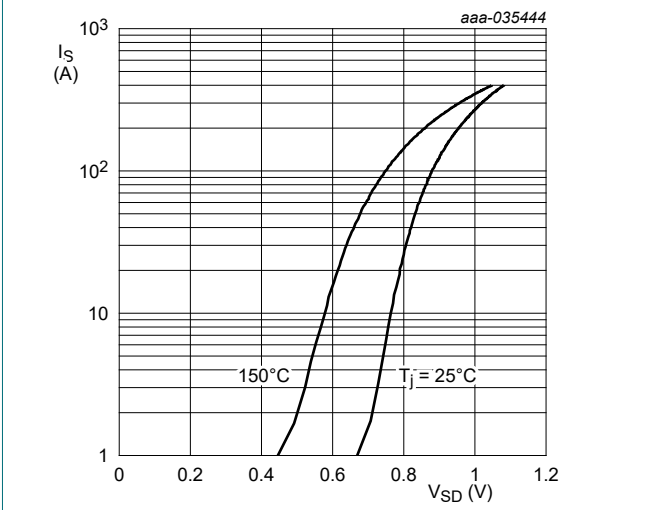


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0 \text{ V}$

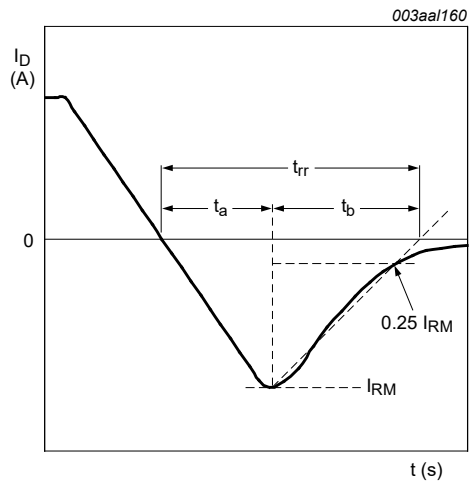


Fig. 16. Reverse recovery timing definition

11. Package outline

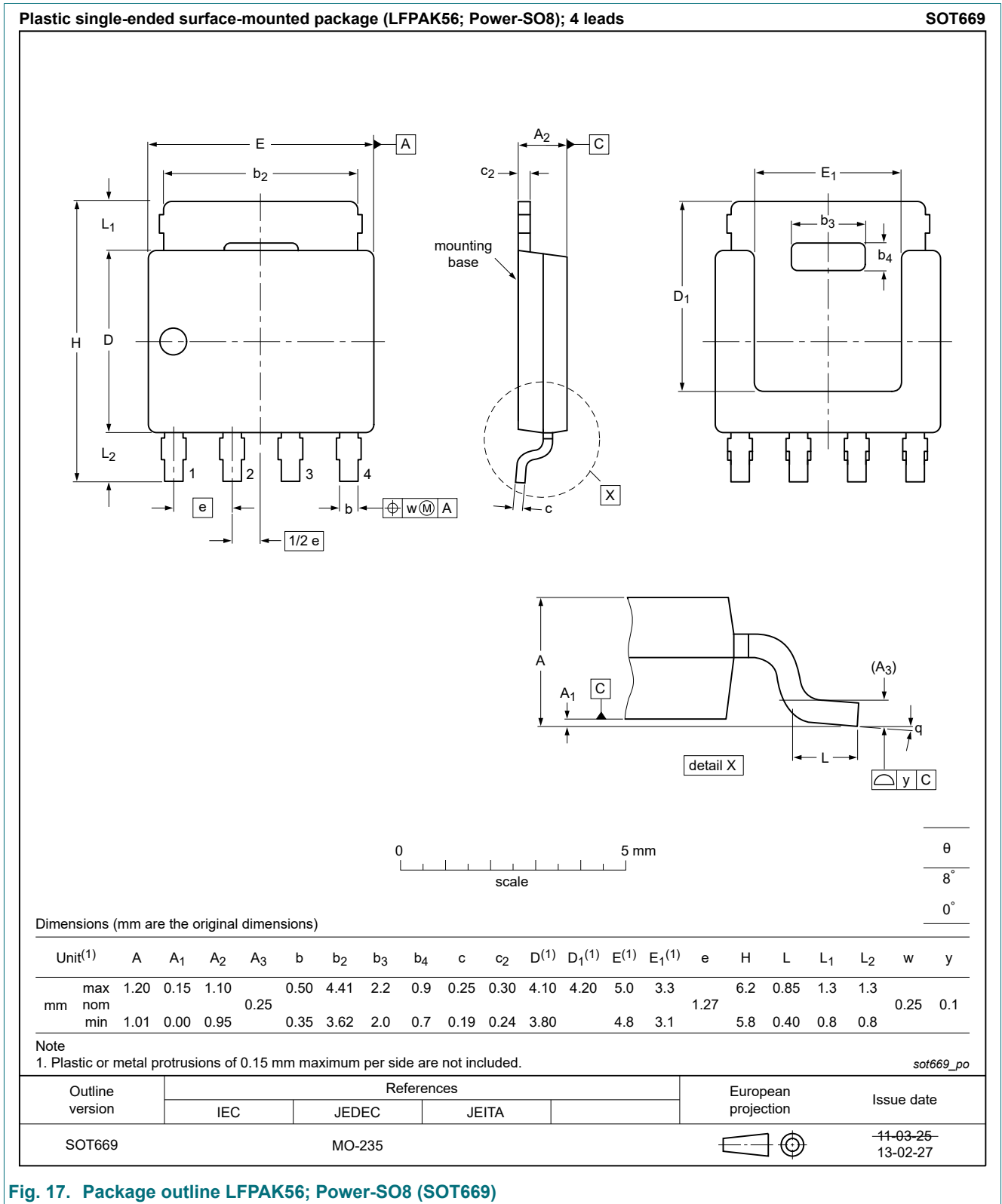


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

12. Soldering

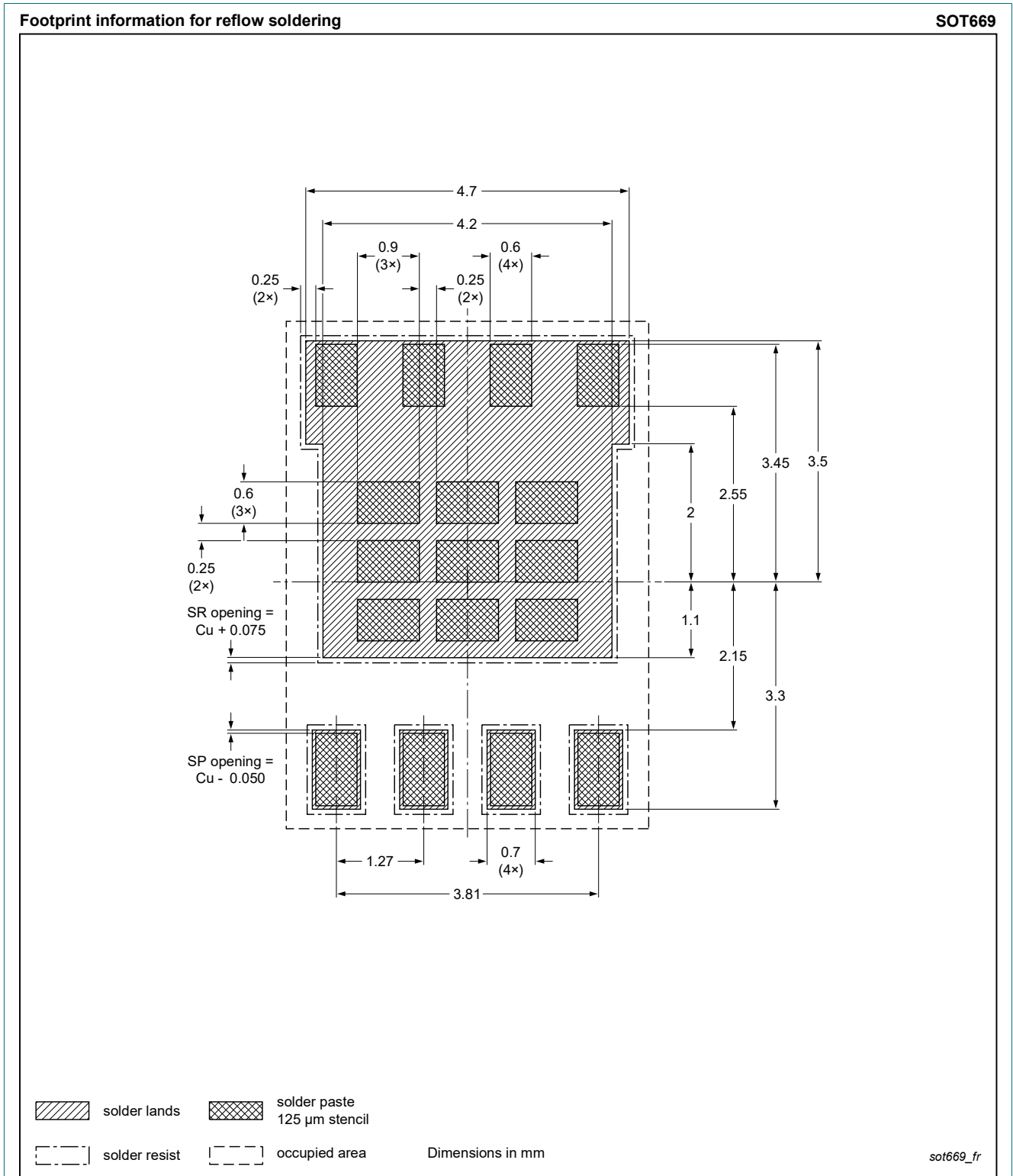
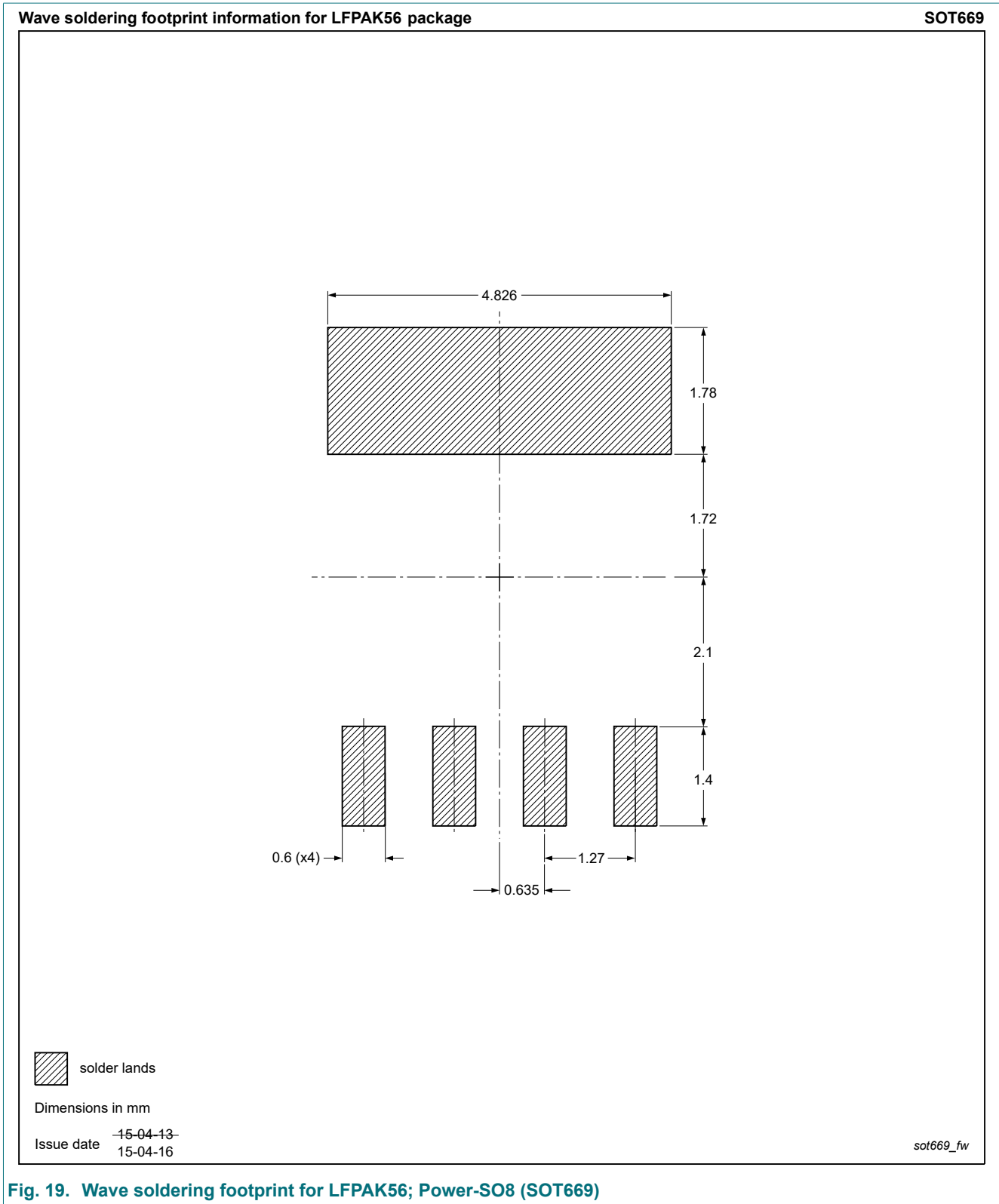


Fig. 18. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)



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|--------------------------------|--------------------|---|
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